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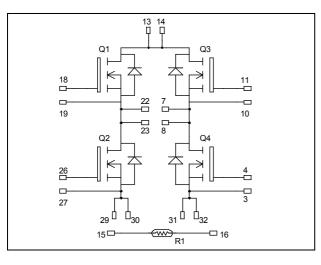
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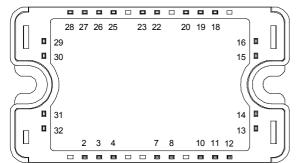




APTM50HM65FT3G

Full - Bridge MOSFET Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

Symbol Parameter Max ratings Unit Drain - Source Breakdown Voltage 500 V V_{DSS} $T_c = 25^{\circ}C$ 51 I_D Continuous Drain Current $T_c = 80^{\circ}C$ 38 Α I_{DM} Pulsed Drain current 204 V Gate - Source Voltage ± 30 V_{GS} Drain - Source ON Resistance 78 R_{DSon} mΩ Maximum Power Dissipation $T_c = 25^{\circ}C$ 390 W P_D 51 Avalanche current (repetitive and non repetitive) I_{AR} А EAR Repetitive Avalanche Energy 50 mJ Single Pulse Avalanche Energy 3000 EAS

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

$V_{DSS} = 500V$ $R_{DSon} = 65m\Omega \text{ typ} @ \text{Tj} = 25^{\circ}\text{C}$ $I_D = 51A @ \text{Tc} = 25^{\circ}\text{C}$

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
 - Kelvin source for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Internal thermistor for temperature monitoring
 - High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

1 - 6

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All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I _{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^{\circ}C$			100	
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125^{\circ}C$			500	μA
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25.5A$		65	78	mΩ
V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5 \text{mA}$	3		5	V
I _{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
C _{iss}	Input Capacitance	$V_{GS} = 0V$		7000		
Coss	Output Capacitance	$V_{\rm DS} = 25V$		1400		pF
C _{rss}	Reverse Transfer Capacitance	f=1MHz		90		
Qg	Total gate Charge	$V_{GS} = 10V$		140		
Q _{gs}	Gate – Source Charge	$V_{Bus} = 250V$		40		nC
Q_{gd}	Gate – Drain Charge	$I_D = 51A$		70		
T _{d(on)}	Turn-on Delay Time	Inductive switching @ 125°C		21		
Tr	Rise Time	$V_{GS} = 15V$ $V_{Bus} = 333V$ $I_D = 51A$ $R_G = 3\Omega$		38		ns
T _{d(off)}	Turn-off Delay Time			75		
$T_{\rm f}$	Fall Time			93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V$, $V_{Bus} = 333V$ $I_D = 51A$, $R_G = 3\Omega$		1035		т
E _{off}	Turn-off Switching Energy			845		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		1556		т
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy			1013		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Is	Continuous Source current		$Tc = 25^{\circ}C$			51	А
	(Body diode)		$Tc = 80^{\circ}C$			38	Л
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -51A$				1.3	V
dv/dt	Peak Diode Recovery 1					15	V/ns
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$			270	ns
	Reverse Recovery Time	$I_{S} = -51A$ $V_{R} = 333V$	$T_{j} = 125^{\circ}C$			540	115
Q _{rr}	Reverse Recovery Charge	$di_{s}/dt = 100 A/\mu s$	$T_j = 25^{\circ}C$		2.6		μC
		~ '	$T_{j} = 125^{\circ}C$		9.6		μΟ

• dv/dt numbers reflect the limitations of the circuit rather than the device itself. $I_S \le -51A$ di/dt $\le 700A/\mu s$ $V_R \le V_{DSS}$ $T_i \le 150^{\circ}C$



Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance					0.32	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range			-40		150	
T _{STG}	Storage Temperature Range			-40		125	°C
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight				110	g	

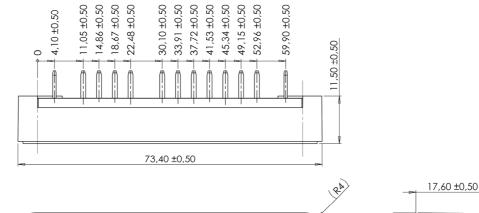
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

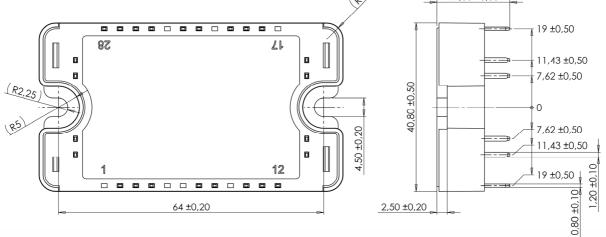
Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$= \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermistor temperature
R_T: Thermistor value at T

SP3 Package outline (dimensions in mm)

 R_T



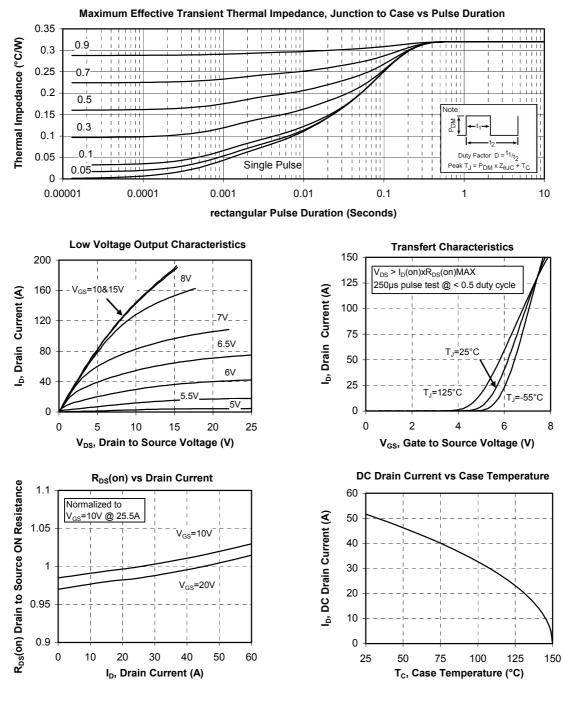


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com



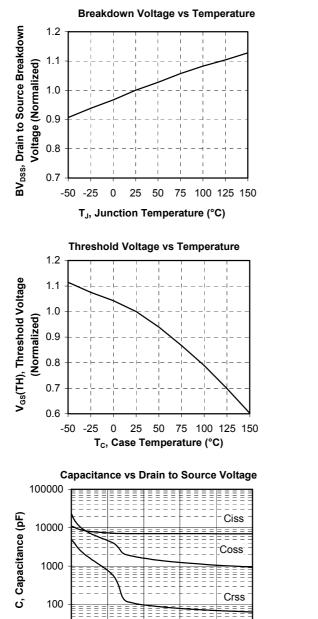
APTM50HM65FT3G

Typical Performance Curve



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10

0

10

20

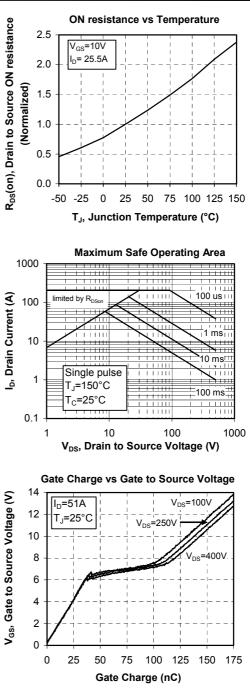
V_{DS}, Drain to Source Voltage (V)

30

40

50

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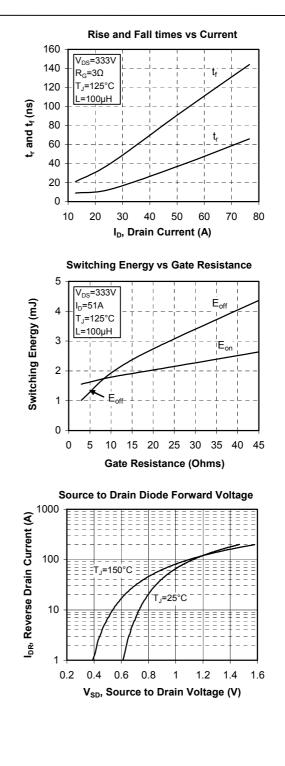




Delay Times vs Current 80 70 td(off) V_{DS}=333 t_{d(on)} and t_{d(off)} (ns) 60 R_G=3Ω T_J=125°C 50 L=100µH 40 30 td(on) 20 10 10 20 30 80 40 50 60 70 I_D, Drain Current (A) Switching Energy vs Current 3 V_{DS}=333V 2.5 R_G=3Ω Switching Energy (mJ) T_=125°C 2 =100µH 1.5 ⁻E_{off} 1 0.5 0 10 20 30 40 50 60 70 80 I_D, Drain Current (A) **Operating Frequency vs Drain Current** 450 V_{DS}=333\ 400 D=50% 350 7VS R_G=3Ω Frequency (kHz) T_=125°C 300 T_C=75°C 250 200 ZCS 150 100 hard 50 switching 0 15 25 30 35 40 10 20 45

I_D, Drain Current (A)

APTM50HM65FT3G





APTM50HM65FT3G

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